

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	448557	(thin film transistor or TFT).clm.	US-PGPUB; USPAT	OR	OFF	2006/09/02 13:47
L5	11792	(thin film transistor or TFT).clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:47
L6	6195	buffer layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:47
L7	19906	(activation OR active OR poly OR polysilicon) layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L8	7789	gate (insulation OR dielectric OR oxide) layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L9	465890	(thickness OR thick OR thin or thicker OR thinner).clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L10	984574	(step OR overetch).clm.	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L11	30982	9 with 10	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L12	130	11 with 6	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:48
L13	54	12 with 4	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:50
L15	1928	4 with 8	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:49
L16	2	13 and 15	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:49
L17	130	12 with 6	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:50
L18	1	13 with 8	US-PGPUB; USPAT	ADJ	OFF	2006/09/02 13:51

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S193	11	(US-20020030228-\$ or US-20040207015-\$ or US-20040211356-\$).did. or (US-5492843-\$ or US-5985704-\$ or US-5310457-\$ or US-4949141-\$ or US-6150203-\$ or US-6794294-\$ or US-5468987-\$).did. or (JP-01128575-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2006/07/07 19:53
S194	7	S193 and (poly polysilicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/07 19:54
S197	25507	(a-silicon amorphous adj silicon) and (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/07 19:57
S198	11838	(a-silicon amorphous adj silicon) near3 (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/07 19:57
S200	6606	(amorphous adj silicon) near (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/07 19:58
S201	126	(amorphous adj silicon) near (polysilicon polycrystalline) and @pd<"19870101"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/07 19:58
S204	4	(protective adj film cap-layer) with amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/08 12:02
S205	4	(protective adj film cap-layer) with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/07/08 12:02
S243	17	method near3 (spc solid phase crystallization)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	ADJ	OFF	2006/08/04 13:26

EAST Search History

S24 4	46	("5492843" "5985704") and (over\$1etch\$3 or (buffer with etch\$3))	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:57
S24 5	179	("5492843" "5985704") and insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:57
S24 6	166	("5492843" "5985704") and gate adj insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:57
S24 7	151	("5492843" "5985704") and thick\$4 with insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 14:57
S24 8	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGPUB; USPAT; JPO	OR	ON	2006/08/25 15:21
S24 9	281	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	USPAT	OR	ON	2006/08/25 15:21
S25 0	7546	"117"/\$3.ccls.	USPAT	OR	ON	2006/08/25 15:21
S25 1	4429	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21
S25 2	7441	(Park-Kee\$ or Yoo-J\$ or Han-M\$). in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21
S25 3	9570	(257/347,350,390,40,51,57,59,66, 72).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/25 15:21
S25 4	4381	S253 and (tft thin adj film adj transistor)	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21
S25 5	1147	S254 and buffer	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21

EAST Search History

S25 6	31577	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21
S25 7	25	"4,767,723"	US-PGPUB; USPAT	OR	ON	2006/08/25 15:21
S25 8	825	"5837619" "5492843" (adachi and tft)	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21
S25 9	40385	gate insulating and gate electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/08/25 15:21
S26 0	3207	etch adj rate near4 (sin silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S26 1	26	"275638"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/08/25 15:21
S26 2	4	"275638" and adachi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/08/25 15:21
S26 3	21	(buffer near conductive) adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/08/25 15:21
S26 4	19	((("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904"))). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/25 15:21

EAST Search History

S26 5	8	(S264 or S248) and (hoon near kim or thin adj film adj transistor or tft)	US-PGPUB; USPAT; JPO	OR	ON	2006/08/25 15:21
S26 7	22	(thin adj film adj transistor or tft) and amorphous adj silicon and S252	USPAT	OR	ON	2006/08/25 15:21
S26 8	46	"4851363" not S253	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21
S26 9	86	S260 and process near4 etching near4 silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S27 0	17	"5,310,457"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S27 1	23	"275,638"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S27 2	3	(US-20040211356-\$).did. or (US-5985704-\$ or US-4949141-\$). did.	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21
S27 3	3	S272 and (thick thicker thickest thickened thicken thickness thin thinner) with (oxide nitride insulator insulating insulated)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21
S27 4	167	hoon near kim	US-PGPUB; USPAT	OR	OFF	2006/08/25 15:21
S27 5	702	(etch etching etchant etched pattern patterned patterning) near4 buffer and (thin adj film adj transistor or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/08/25 15:21
S27 6	1405	S251 and "257"/\$3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21

EAST Search History

S27 7	3625	S251 and step not step adj for	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 15:21
S27 9	11	(US-20020030228-\$ or US-20040207015-\$ or US-20040211356-\$).did. or (US-5492843-\$ or US-5985704-\$ or US-5310457-\$ or US-4949141-\$ or US-6150203-\$ or US-6794294-\$ or US-5468987-\$).did. or (JP-01128575-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2006/08/25 15:21
S28 0	7	S279 and (poly polysilicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 1	26071	(a-silicon amorphous adj silicon) and (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 2	12105	(a-silicon amorphous adj silicon) near3 (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 3	130	(amorphous adj silicon) near (polysilicon polycrystalline) and @pd<"19870101"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 4	6779	(amorphous adj silicon) near (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 5	4	(protective adj film cap-layer) with amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 6	4	(protective adj film cap-layer) with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21

EAST Search History

S28 7	676	amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S28 8	36	amorphous with thermal adj crystallization with thickness	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21
S29 0	36	amorphous with thermal adj crystallization with thickness and thickness with (polysilicon silicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/25 15:21